<u> </u>	r	Constant Mark	Dr	I Million of a second
L Number	Hits		DB	Time stamp
1	679	(((substrate wafer semiconductor) and	USPAT;	2001/12/13 11:54
		(passivat\$3 (silicon adj2 nitride) Si3N4	US-PGPUB	
		("Si.sib.3" adj "N.sub.4"))) and		
		photoresist) and (photoresist with		1
		(reflow\$3 flow\$4))		
2	22		EPO; JPO;	2001/12/13 11:56
		(passivat\$3 (silicon adj2 nitride) Si3N4	DERWENT;	
		("Si.sib.3" adj "N.sub.4"))) and	IBM TDB	
		photoresist) and (photoresist with		
		(reflow\$3 flow\$4))		/ /
-	522159	substrate wafer semiconductor	USPAT;	2001/12/11 17:11
			US-PGPUB	
[-	49945		USPAT;	2001/12/11 17:11
		(passivat\$3 (silicon adj2 nitride) Si3N4	US-PGPUB	
		("Si.sib.3" adj "N.sub.4"))		
] -	17785	((substrate wafer semiconductor) and	USPAT;	2001/12/11 17:11
i		(passivat\$3 (silicon adj2 nitride) Si3N4	US-PGPUB	
		("Si.sib.3" adj "N.sub.4"))) and		
]		photoresist		0000 (10 (22 22 22
-	1522		USPAT;	2001/12/11 16:36
		(passivat\$3 (silicon adj2 nitride) Si3N4	US-PGPUB	
		("Si.sib.3" adj "N.sub.4"))) and		
		photoresist) and reflow\$3		0001/10/11 16 53
-	155	((((substrate wafer semiconductor) and	USPAT;	2001/12/11 16:53
		(passivat\$3 (silicon adj2 nitride) Si3N4	US-PGPUB	
		("Si.sib.3" adj "N.sub.4"))) and	Ì	
		photoresist) and reflow\$3) and tape		0000 (00 (00 10 10 10 10
-	121		USPAT;	2001/12/11 17:11
		(passivat\$3 (silicon adj2 nitride) Si3N4	US-PGPUB	
		("Si.sib.3" adj "N.sub.4"))) and		
		photoresist) and (photoresist with		
		reflow\$3)		0001/10/11 17 11
-	1598500	substrate wafer semiconductor	EPO; JPO;	2001/12/11 17:11
			DERWENT;	
	00010		IBM TDB	2001/12/11 17:11
_	32212	(substrate wafer semiconductor) and	EPO; JPO; DERWENT;	2001/12/11 17:11
		(passivat\$3 (silicon adj2 nitride) Si3N4		
	2202	("Si.sib.3" adj "N.sub.4"))	IBM TDB EPO; JPO;	2001/12/11 17:11
-	2389	((substrate wafer semiconductor) and (passivat\$3 (silicon adj2 nitride) Si3N4	DERWENT;	2001/12/11 1/:11
			IBM TDB	
		("Si.sib.3" adj "N.sub.4"))) and photoresist	TON TOB	1
_	11	•	EPO; JPO;	2001/12/11 17:13
-	11	(((Substrate water semiconductor) and (passivat\$3 (silicon adj2 nitride) Si3N4	DERWENT;	2001/12/11 17.13
		("Si.sib.3" adj "N.sub.4"))) and	IBM TDB	
		photoresist) and (photoresist with	1511 155	
		reflow\$3)		
_	21		EPO; JPO;	2001/12/11 17:13
-	21	(((substrate water semiconductor) and (passivat\$3 (silicon adj2 nitride) Si3N4	DERWENT;	2501/12/11 17.13
		("Si.sib.3" adj "N.sub.4"))) and	IBM TDB	
		photoresist) and (photoresist with	TON TOD	
ı		(reflow\$3 flow\$3))	I	<u> </u>